

APPENDIX

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE TITLE:

The title is changed as follows:

**SOLID-STATE IMAGE PICKUP DEVICE HAVING IMPROVED FLATNESS
AND METHOD FOR FABRICATING THE SAME**

IN THE CLAIMS:

The claims are amended as follows:

1. (Amended) A solid-state image pickup device comprising
first and second insulating films formed on a surface of a semiconductor substrate,
a solid-state image pickup region having, as a charge transfer electrode, an electrically
conductive [single-layer] material film formed on said first insulating film, and
a peripheral circuit region formed on said semiconductor substrate other than in said
solid-state image pickup region, a device in said peripheral circuit region being isolated from
another device by means of an isolating electrode on said second insulating film, and said
isolating electrode being formed of said [single-layer] conductive material film.

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8. (Amended) The solid-state image pickup device according to claim 6, wherein said third insulating film is thinner than said [first] second insulating film, and said [second] third insulating film has the same thickness as said first insulating film.

15. (Amended) The solid-state image pickup device according to claim 11, wherein said second diffusion layer is formed to be separated into at least two regions on the semiconductor substrate below said isolating electrode, and
at least one of the at least two regions is connected to said isolating electrode.

16. (Amended) The solid-state image pickup device according to claim 12, wherein said second diffusion layer is formed to be separated into at least two regions on the semiconductor substrate below said isolating electrode, and
at least one of the at least two regions is connected to said isolating electrode.

17. (Amended) The solid-state image pickup device according to claim 13, wherein said second diffusion layer is formed to be separated into at least two regions on the semiconductor substrate below said isolating electrode, and
at least one of the at least two regions is connected to said isolating electrode.

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18. (Amended) The solid-state image pickup device according to claim 14, wherein
said second diffusion layer is formed to be separated into at least two regions on the
semiconductor substrate below said isolating electrode, and
at least one of the at least two regions is connected to said isolating electrode.

21. (Amended) The solid-state image pickup device according to claim 1, wherein
said electrically conductive [single-layer] material film is formed of a layered film of a
polysilicon film and a metal silicide film formed on the polysilicon film.

22. (Amended) The solid-state image pickup device according to claim 6, wherein
said electrically conductive [single-layer] material film is formed of a layered film of a
polysilicon film and a metal silicide film formed on the polysilicon film.

23. (Amended) The solid-state image pickup device according to claim 5, wherein
said electrically conductive [single-layer] material film is formed of a metal film.

24. (Amended) The solid-state image pickup device according to claim 6, wherein
said electrically conductive [single-layer] material film is formed of a metal film.

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25. (Amended) The solid-state image pickup device according to claim 1, wherein
a fourth insulating film is buried between electrodes formed of said electrically
conductive [single-layer] material film, and

a surface of the semiconductor substrate comprising said electrodes and said fourth
insulating film is made generally flat.

26. (Amended) The solid-state image pickup device according to claim 6, wherein
a fourth insulating film is buried between electrodes formed of said electrically
conductive [single-layer] material film, and
a surface of the semiconductor substrate comprising said electrodes and said fourth
insulating film is made generally flat.

38. (Amended) The method for fabricating a solid-state image pickup device according
to claim 29, wherein
the step of patterning said electrically conductive electrode material film is followed by
[the] a step of burying a fourth insulating film between electrodes formed of said electrically
conductive electrode material film including said charge transfer electrode and said isolating
electrode.

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39. (Amended) The method for fabricating a solid-state image pickup device according to claim 35, wherein

the step of patterning said electrically conductive electrode material film is followed by [the] a step of burying a fourth insulating film between electrodes formed of said electrically conductive electrode material film including said charge transfer electrode and said isolating electrode.

40. (Amended) The method for fabricating a solid-state image pickup device according to claim 36, wherein

the step of patterning said electrically conductive electrode material film is followed by [the] a step of burying a fourth insulating film between electrodes formed of said electrically conductive electrode material film including said charge transfer electrode and said isolating electrode.